3.5x2.8mm PHOTOTRANSISTOR

Part Number: AA3528P3S

Features

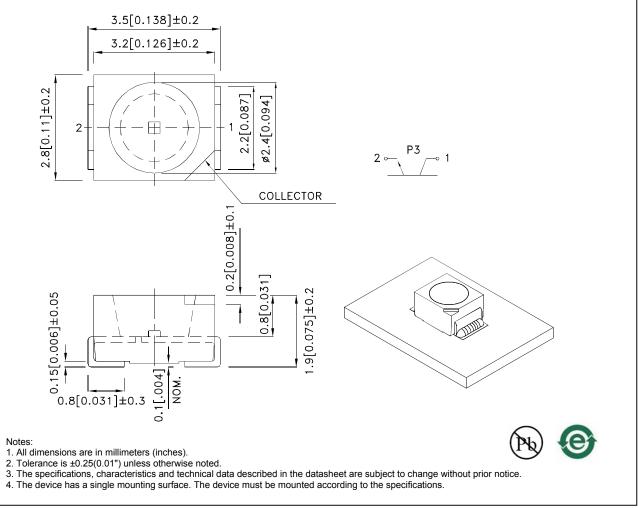
• Mechanically and spectrally matched to the infrared emitting LED lamp.

- Package : 2000pcs / reel.
- Moisture sensitivity level : level 3.
- RoHS compliant.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions

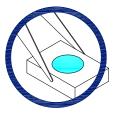


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Handling Precautions

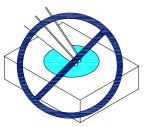
Compare to epoxy encapsulant that is hard and brittle, silicone is softer and flexible. Although its characteristic significantly reduces thermal stress, it is more susceptible to damage by external mechanical force. As a result, special handling precautions need to be observed during assembly using silicone encapsulated LED products. Failure to comply might lead to damage and premature failure of the LED.

1. Handle the component along the side surfaces by using forceps or appropriate tools.

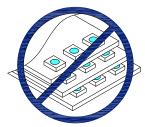


2. Do not directly touch or handle the silicone lens surface. It may damage the internal circuitry.

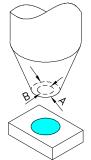




3. Do not stack together assembled PCBs containing exposed LEDs. Impact may scratch the silicone lens or damage the internal circuitry.



- 4.1. The inner diameter of the SMD pickup nozzle should not exceed the size of the LED to prevent air leaks.
- 4.2. A pliable material is suggested for the nozzle tip to avoid scratching or damaging the LED surface during pickup.
- 4.3. The dimensions of the component must be accurately programmed in the pick-and-place machine to insure precise pickup and avoid damage during production.



5. As silicone encapsulation is permeable to gases, some corrosive substances such as H_2S might corrode silver plating of leadframe. Special care should be taken if an LED with silicone encapsulation is to be used near such substances.

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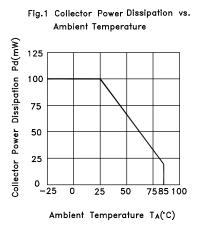
Electrical / Optical Characteristics at TA=25°C

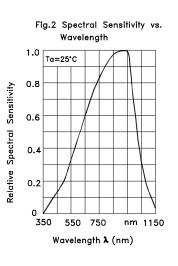
Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
VBR CEO	Collector-to-Emitter Breakdown Voltage	30			v	Ic=100uA Ee=0mW/c
VBR ECO	Emitter-to-Collector Breakdown Voltage	5			v	le=100uA Ee=0mW/c
VCE (SAT)	Collector-to-Emitter Saturation Voltage			0.8	v	lc=2mA Ee=20mW/c mঁ
I CEO	Collector Dark Current			100	nA	Vce=10V Ee=0mW/c mំ
TR	Rise Time (10% to 90%)		15		us	Vce = 5V Ic=1mA RL=1000Ω
TF	Fall Time (90% to 10%)		15		us	
I (ON)	On State Collector Current	0.2	0.4		mA	Vce = 5V Ee=1mW/c m³ λ=940nm

Absolute Maximum Ratings at TA=25°C

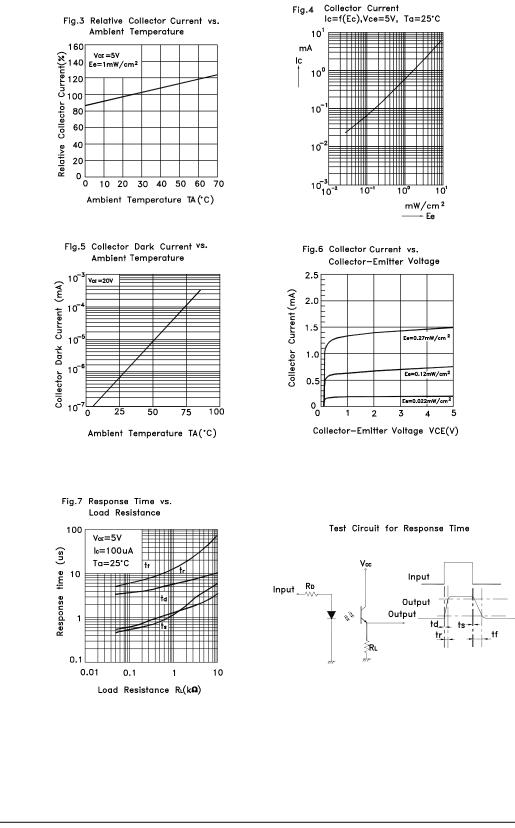
Parameter	Max.Ratings		
Collector-to-Emitter Voltage	30V		
Emitter-to-Collector Voltage	5V		
Power Dissipation at (or below) 25°C Free Air Temperature	100mW		
Operating Temperature	-40°C To +85°C		
Storage Temperature	-40°C To +85°C		





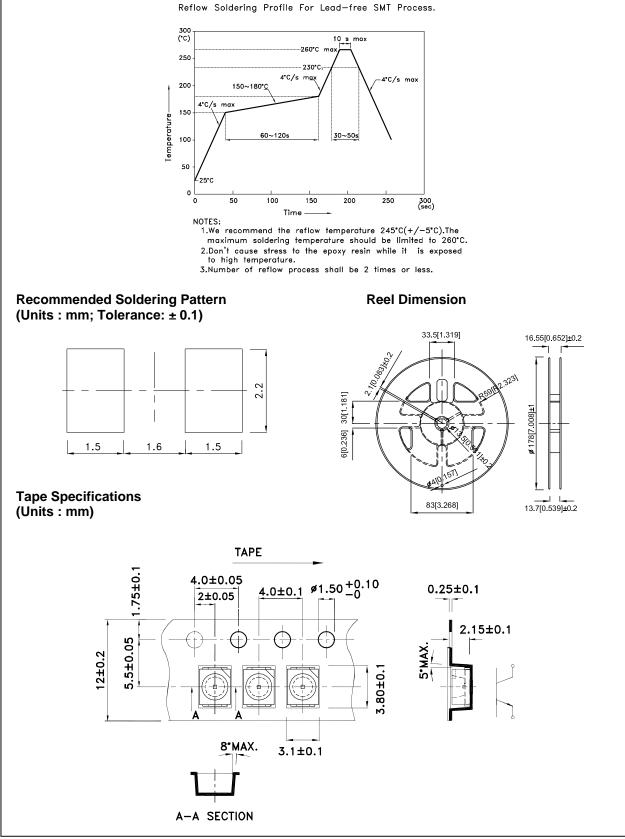


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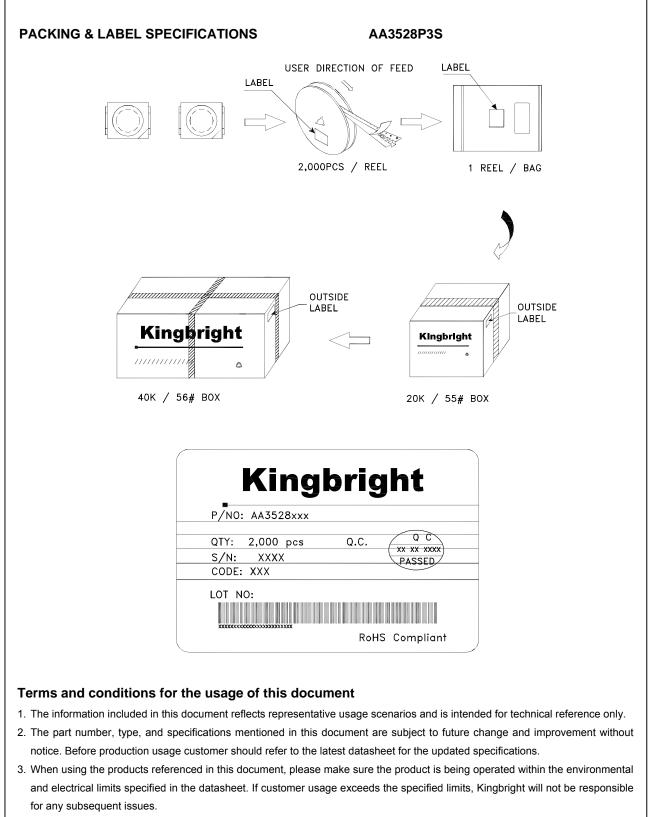
Reflow soldering is recommended and the soldering profile is shown below. Other soldering methods are not recommended as they might cause damage to the product.



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- 4. The information in this document applies to typical usage in consumer electronics applications. If customer's application has special reliability requirements or have life-threatening liabilities, such as automotive or medical usage, please consult with Kingbright representative for further assistance.
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